

350mA 40V(0.47mm)

### Chip Information

Chip Size	0.47 x 0.47mm
Pad Size	0.31 x 0.31mm
Chip Quantity	49966 pcs/wafer
Scribe Line Width	60um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

### MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	40	V	
Average Forward Rectified Current	IF(AV)	350	mA	
Peak Forward Surge Current	IFSM	1.5	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

### ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.590	0.570	0.470	V	IF=200mA Ta=25degC
	VF2	0.370	0.360	0.340	V	IF=20mA Ta=25degC
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	5	2	0.6	uA	VR=30V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	42	44	55	V	IR=10uA
Junction Capacitance	Cj			50	pF	V=0V,f=1MHz
Reverse Recovery Time	trr			6.4	nS	IF=IR=10mA irr=0.1IR

### Ordering Information

Chip Type	Chip Thickness	Back Metal
XHH095	180 +/- 20um	Au(For Eutectic)
XHH097	150 +/- 20um	Au(For Eutectic)
XHH096	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:  
Designed For SD103AW-CW